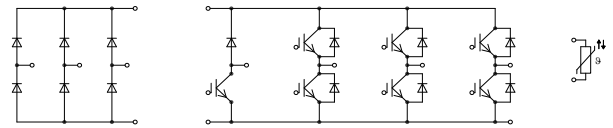
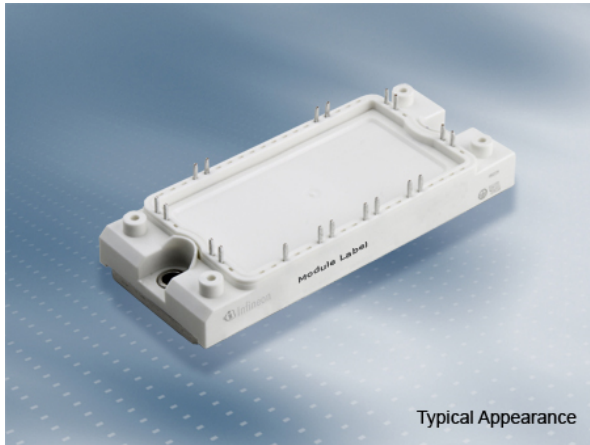


EconoPIM™2 模块 采用第四代沟槽栅/场终止IGBT4和第四代发射极控制二极管 带有温度检测NTC 和预涂导热介质
 EconoPIM™2 module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode and NTC / pre-applied Thermal Interface Material



$V_{CES} = 1200V$
 $I_{C\ nom} = 50A / I_{CRM} = 100A$

典型应用

- 电机传动
- 伺服驱动器

电气特性

- 提高工作结温 $T_{vj\ op}$
- 低开关损耗
- $T_{vj\ op} = 150^{\circ}C$
- 沟槽栅IGBT4

机械特性

- 高功率循环和温度循环能力
- 集成NTC温度传感器
- 绝缘的基板
- 铜基板
- 焊接技术
- 符合RoHS
- 标准封装
- 预涂导热介质

Typical Applications

- Motor drives
- Servo drives

Electrical Features

- Extended operating temperature $T_{vj\ op}$
- Low switching losses
- $T_{vj\ op} = 150^{\circ}C$
- Trench IGBT 4

Mechanical Features

- High power and thermal cycling capability
- Integrated NTC temperature sensor
- Isolated base plate
- Copper base plate
- Solder contact technology
- RoHS compliant
- Standard housing
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_H = 80^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	50	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	100	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,85 2,15 2,25	2,15	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 1,70\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80	6,40	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,38			μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	4,0			Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	2,80			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,10			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,16 0,17 0,17			μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,03 0,04 0,04			μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,33 0,43 0,45			μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,08 0,15 0,17			μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, L_S = 20\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 1400\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	5,70 7,70 8,40			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, L_S = 20\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3600\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 15\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	2,80 4,30 4,80			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		I_{SC}	180			A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			0,671	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	50	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	100	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	560	A ² s

特征值 / Characteristic Values

		min.	typ.	max.	
正向电压 Forward voltage	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$		1,70	2,15	V
	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$		1,65		V
	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$		1,65		V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 50\text{ A}, -di_F/dt = 1400\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$		54,0		A
	$V_R = 600\text{ V}$		60,0		A
	$V_{GE} = -15\text{ V}$		63,0		A
恢复电荷 Recovered charge	$I_F = 50\text{ A}, -di_F/dt = 1400\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$		5,50		μC
	$V_R = 600\text{ V}$		8,80		μC
	$V_{GE} = -15\text{ V}$		10,0		μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 50\text{ A}, -di_F/dt = 1400\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$		1,70		mJ
	$V_R = 600\text{ V}$		3,00		mJ
	$V_{GE} = -15\text{ V}$		3,70		mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material	R_{thJH}		0,887	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

二极管, 整流器 / Diode, Rectifier 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_H = 70^{\circ}\text{C}$	I_{FRMSM}	70	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_H = 70^{\circ}\text{C}$	I_{RMSM}	80	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$	I_{FSM}	450	A
	$t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$		370	A
I ² t-值 I ² t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1000	A ² s
			685	A ² s

特征值 / Characteristic Values

		min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 50\text{ A}$	V_F	1,05		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$	I_R	1,00		mA
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material	R_{thJH}		0,999	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

IGBT, 制动-斩波器 / IGBT, Brake-Chopper 最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_H = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	25	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	50	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

		min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 25\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,85 2,15 2,25	2,15 V V V
栅极阈值电压 Gate threshold voltage	$I_C = 0,85\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	5,20	5,80	6,40 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$	Q_G	0,20		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}	0,0		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{ies}	1,45		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{res}	0,05		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{CES}			1,0 mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{GES}			100 nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,05 0,06 0,06	μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,03 0,04 0,05	μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,34 0,43 0,45	μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,05 0,07 0,08	μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L_S = 20\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	2,00 2,65 2,90	mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L_S = 20\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1,40 2,20 2,40	mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\max} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	90		A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material	R_{thJH}			0,959 K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{op}}$	-40		150 $^{\circ}\text{C}$

二极管，制动-斩波器 / Diode, Brake-Chopper 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	15	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	30	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	48,0	A ² s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,75	2,15	V
	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	V_F	1,75		V
	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,75		V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 15\text{ A} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		20,0		A
		$T_{vj} = 125^{\circ}\text{C}$	I_{RM}	22,0		A
		$T_{vj} = 150^{\circ}\text{C}$		23,0		A
恢复电荷 Recovered charge	$I_F = 15\text{ A} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,50		μC
		$T_{vj} = 125^{\circ}\text{C}$	Q_r	2,50		μC
		$T_{vj} = 150^{\circ}\text{C}$		2,70		μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 15\text{ A} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		0,55		mJ
		$T_{vj} = 125^{\circ}\text{C}$	E_{rec}	0,90		mJ
		$T_{vj} = 150^{\circ}\text{C}$		1,00		mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material	R_{thJH}			1,65	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
R100 偏差 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

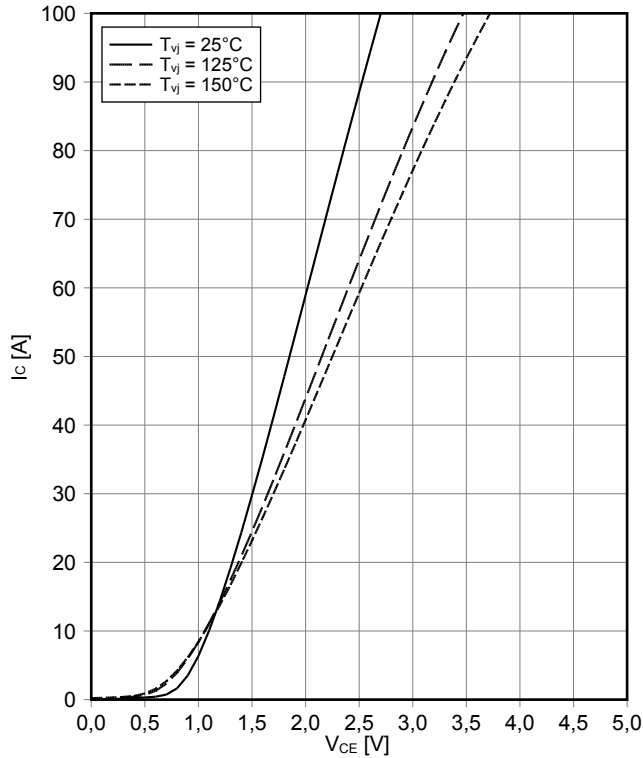
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		10,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		7,5		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
			min.	typ.	max.
杂散电感, 模块 Stray inductance module		L _{sCE}		35	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _H = 25°C, 每个开关 / per switch	R _{CC'+EE'} R _{AA'+CC'}		4,00 3,00	mΩ
储存温度 Storage temperature		T _{stg}	-40		125 °C
最高基板工作温度 Maximum baseplate operation temperature		T _{BPmax}			125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00		6,00 Nm
重量 Weight		G		180	g

Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
Storage and shipment of modules with TIM => see AN2012-07

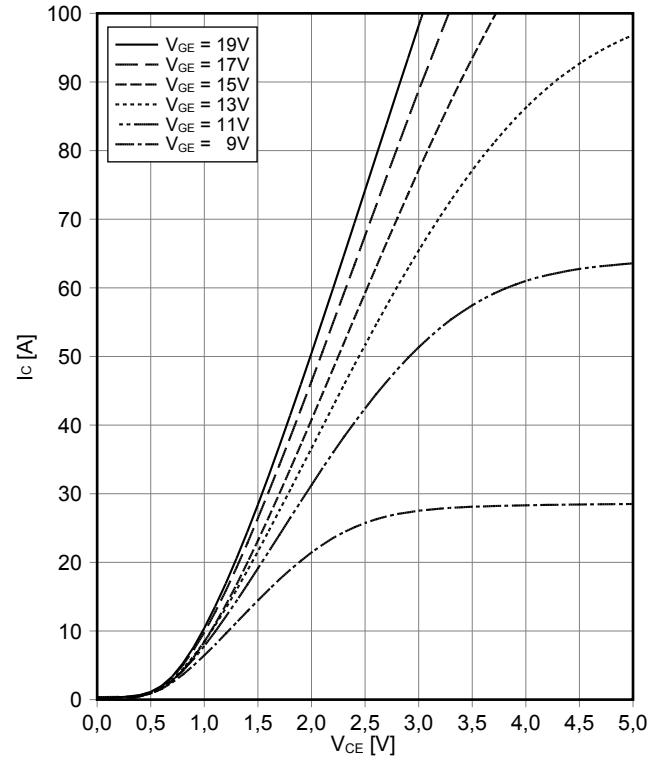
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



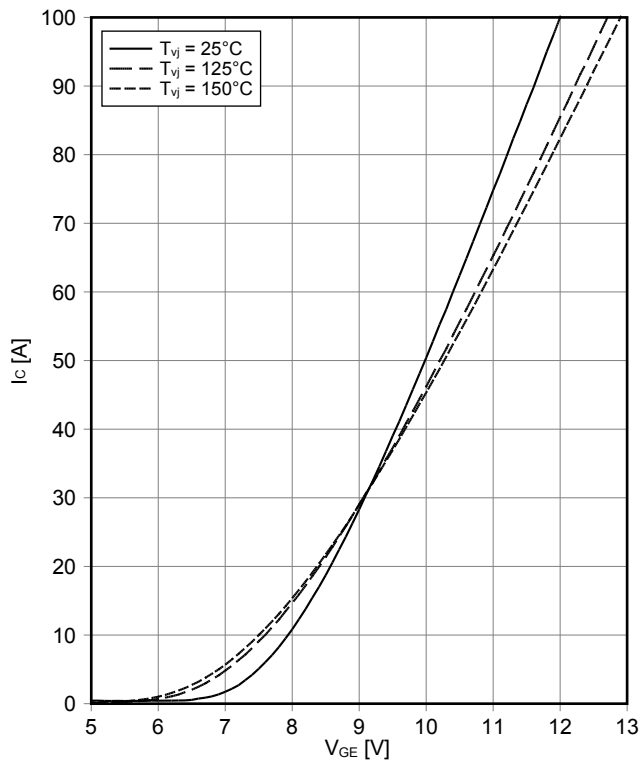
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



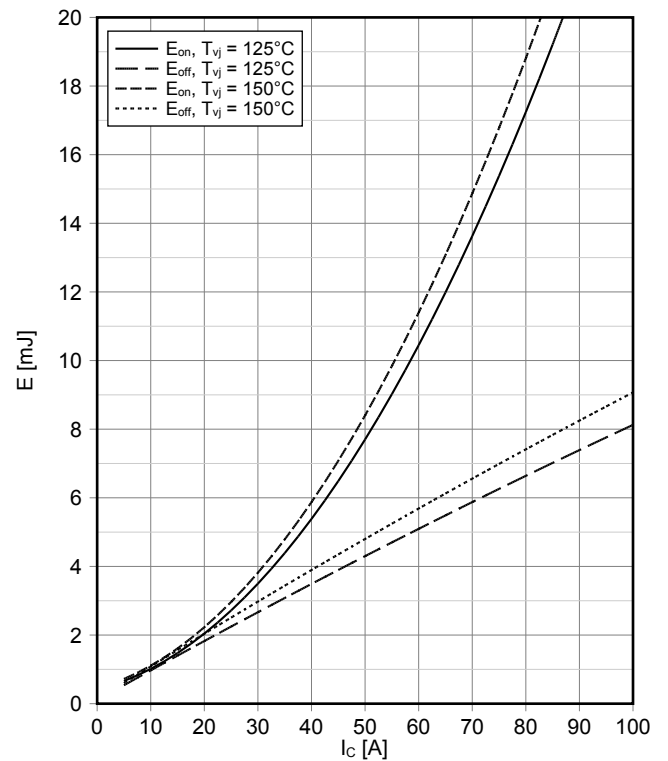
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



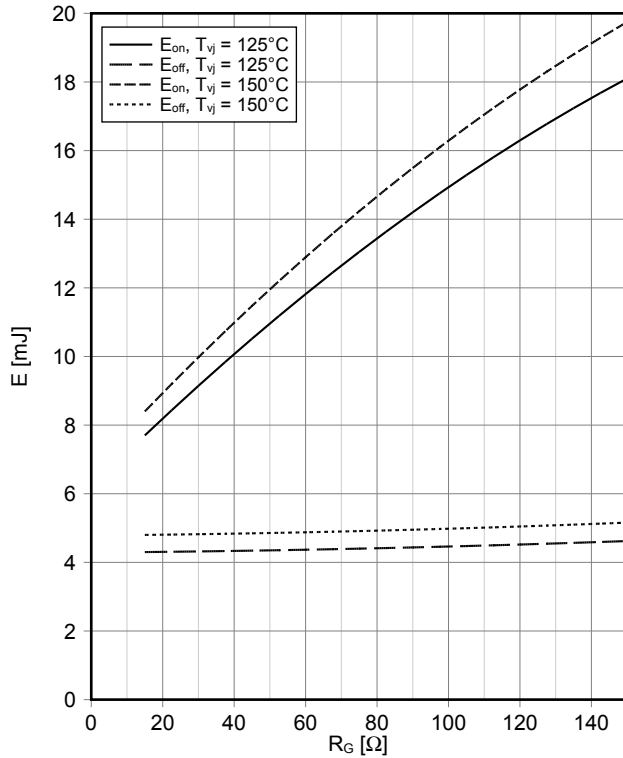
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 15\ \Omega$, $R_{Goff} = 15\ \Omega$, $V_{CE} = 600\text{ V}$

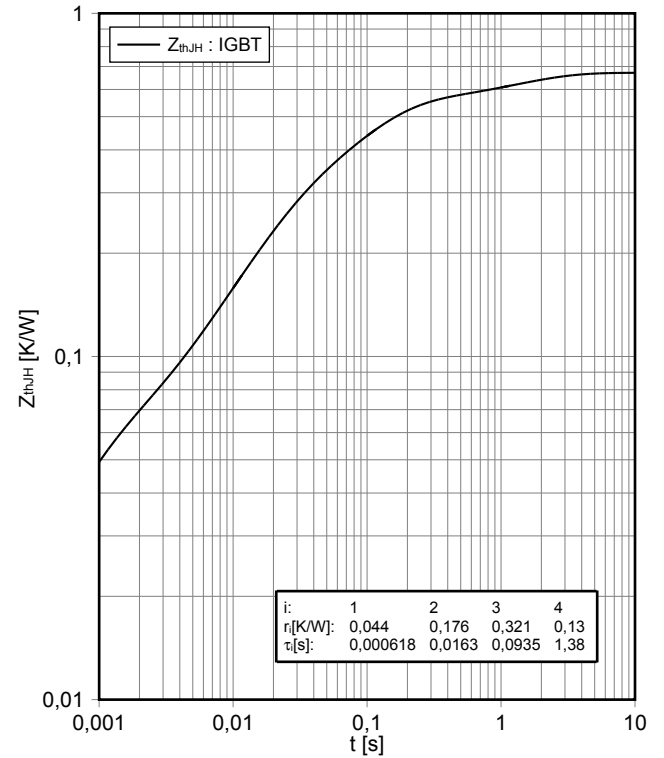


开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 50\text{ A}, V_{CE} = 600\text{ V}$

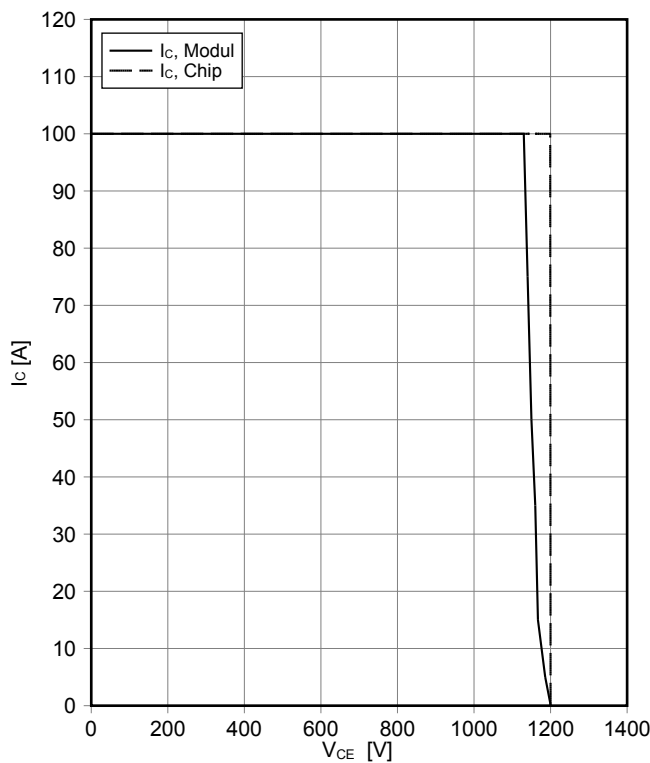


瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter
 $Z_{thJH} = f(t)$

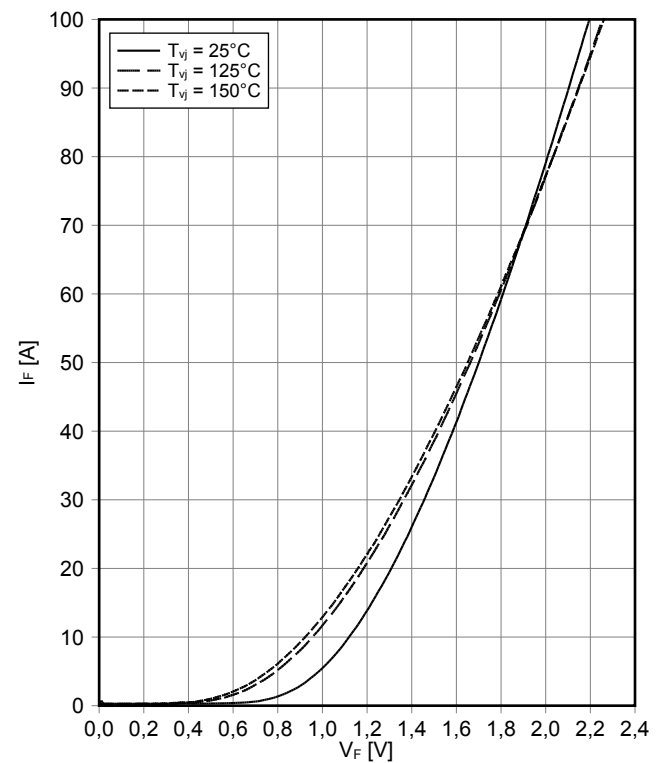


反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 15\ \Omega, T_{vj} = 150^\circ\text{C}$

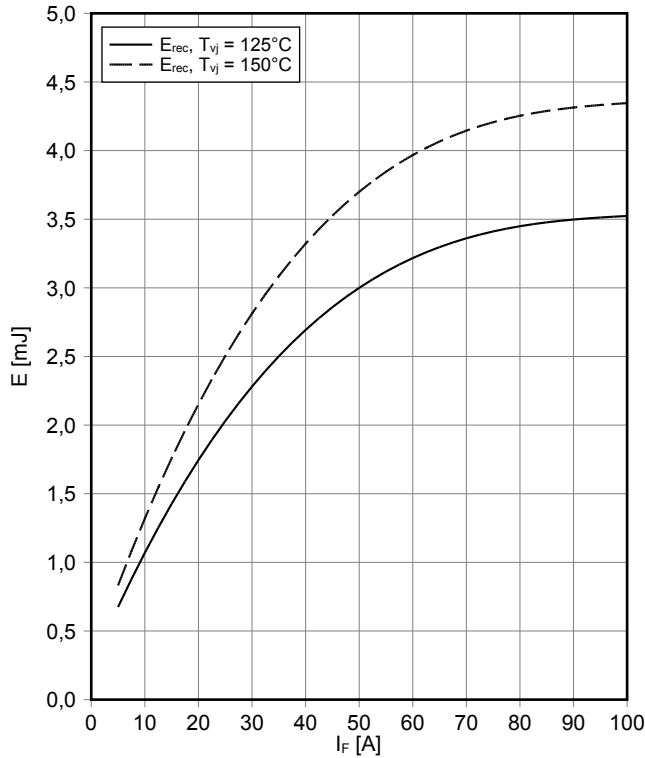


正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)
 $I_F = f(V_F)$



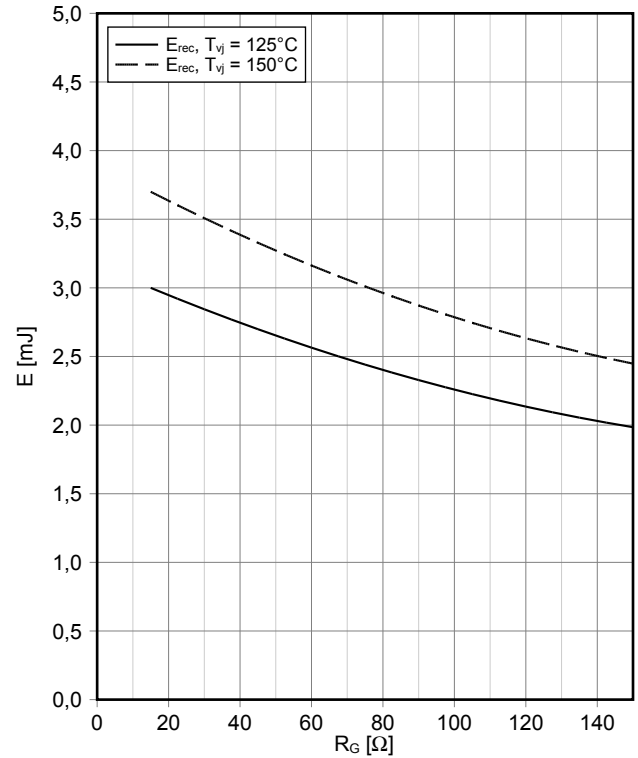
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 15 \Omega, V_{CE} = 600 V$



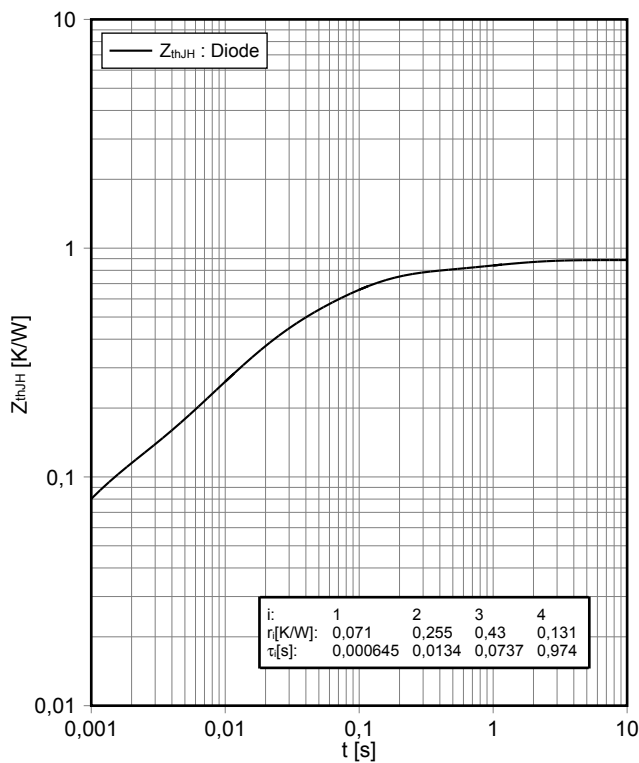
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 50 A, V_{CE} = 600 V$



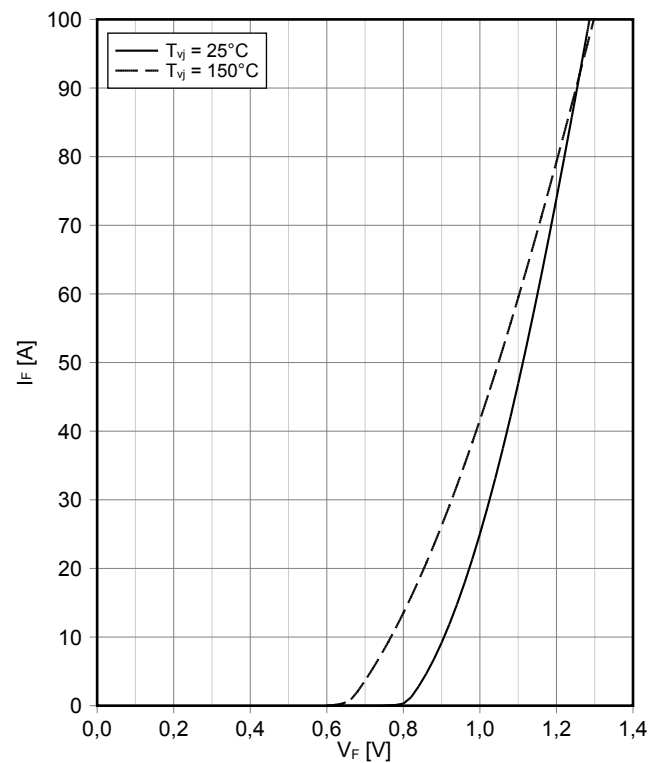
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter

$Z_{thJH} = f(t)$

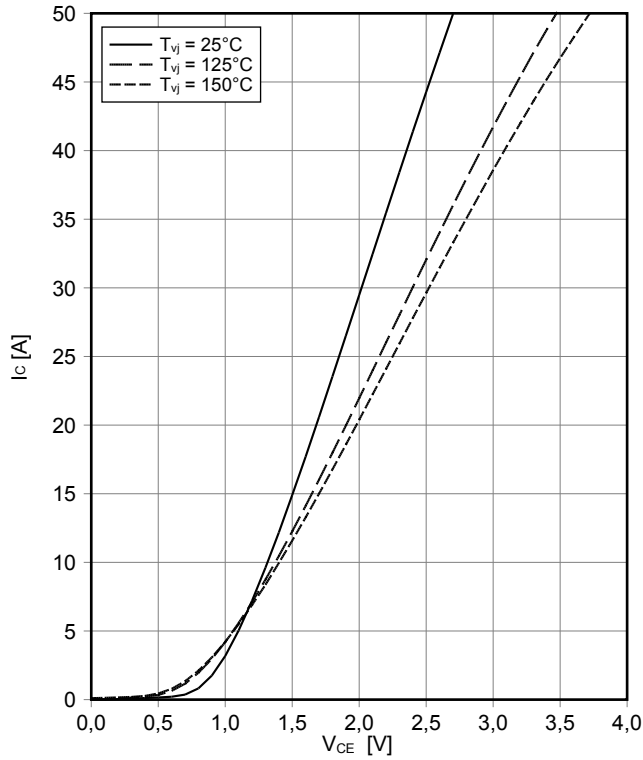


正向偏压特性 二极管,整流器 (典型)
forward characteristic of Diode, Rectifier (typical)

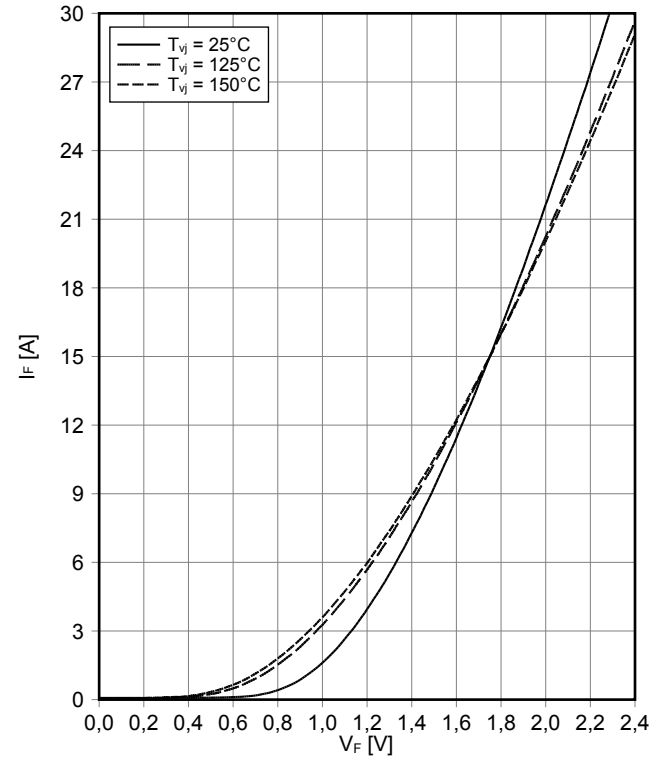
$I_F = f(V_F)$



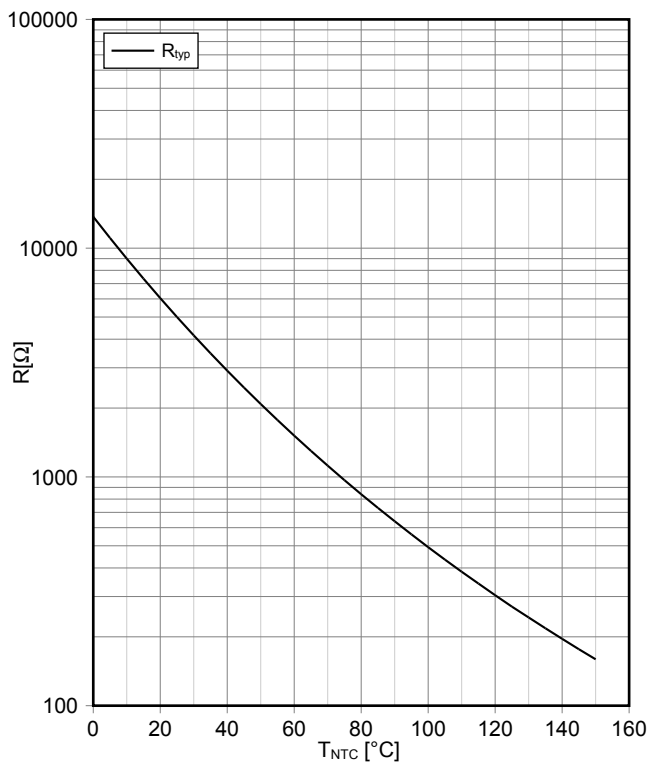
输出特性 IGBT, 制动-斩波器 (典型)
output characteristic IGBT, Brake-Chopper (typical)
 $I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



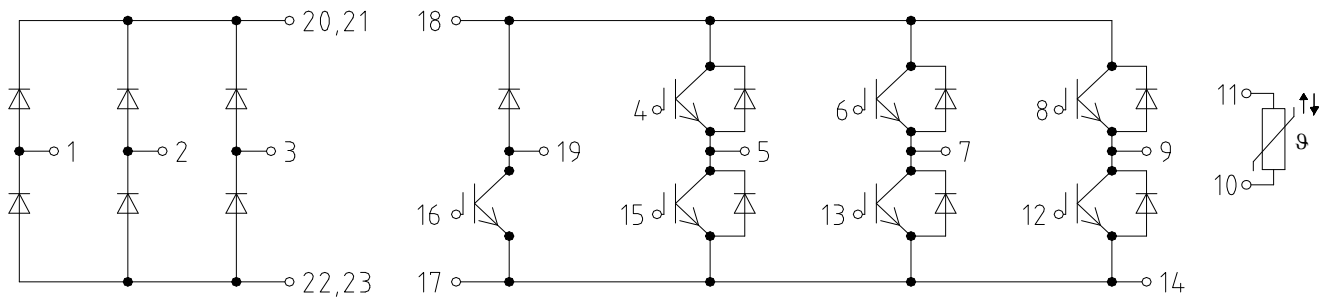
正向偏压特性 二极管, 制动-斩波器 (典型)
forward characteristic of Diode, Brake-Chopper (typical)
 $I_F = f(V_F)$



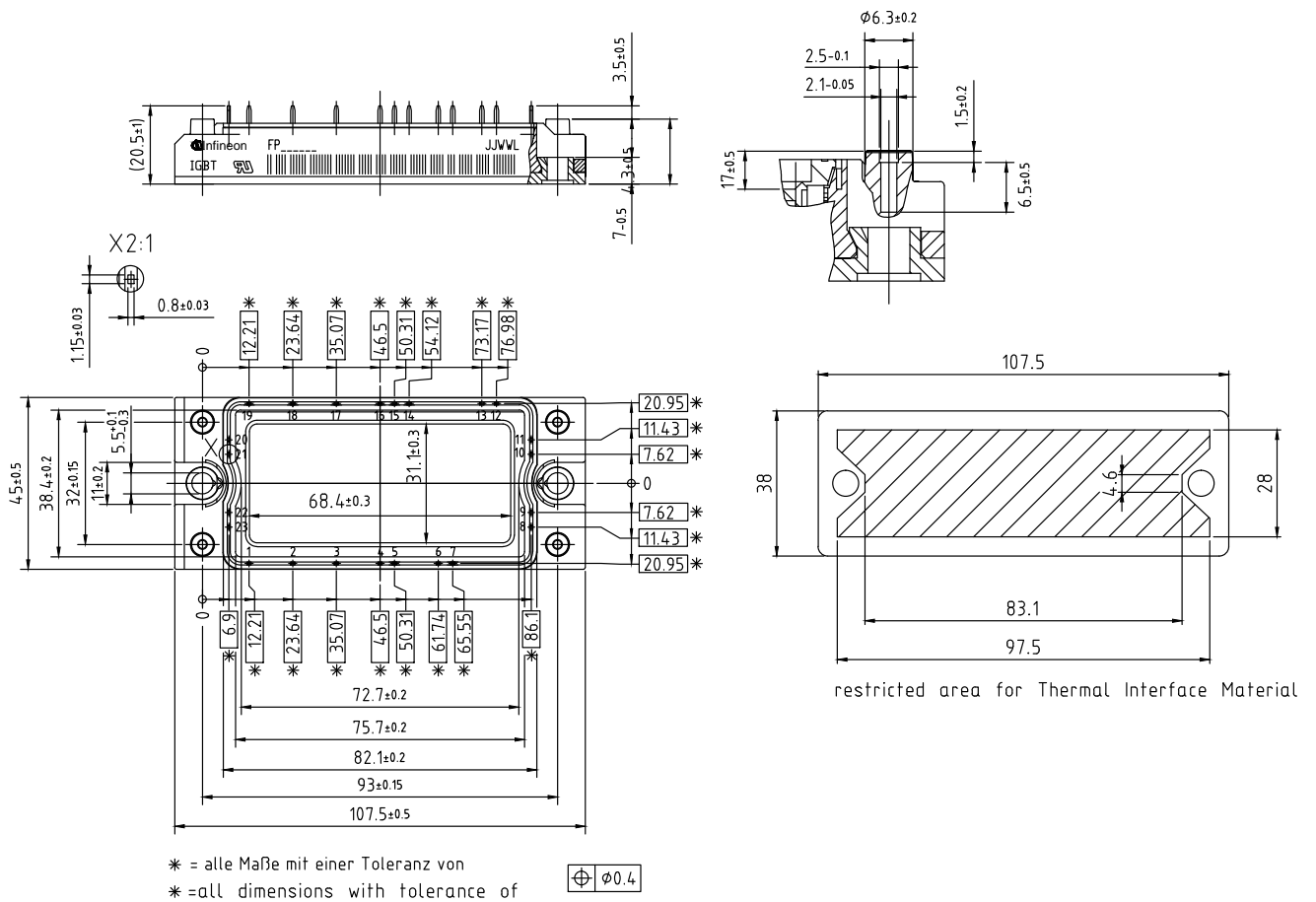
负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



接线图 / Circuit diagram



封装尺寸 / Package outlines



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Edition 2017-03-17

Published by
Infineon Technologies AG
81726 München, Germany

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